

Irradiation-induced Effects in Nuclear Materials Case Study of Nuclear Fuels Frederico Garrido

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EXPERIMENTAL SIMULATION USING ION BEAMS





using ion-beams platforms (GANIL, MOSAIC, ...)





Better understanding of the behaviour of nuclear materials using energetic ion beams

- Irradiation-induced effects: radiation defects, (micro)-structural transformations
- Role played by embedded impurities: fission products, gases (He, Kr, Xe) lattice location and behaviour (T, irradiation, solubility, chemical interaction)
- Ultra simplified system: single crystals
- Parametric approach
- Coupling of experiments and computational tools

Better understanding of the nuclear materials using energetic ion beams: towards the Modelling of Radiation-Induced Effects in Nuclear Materials

Nuclear fuel exhibits the fluorite-type structure

Structure of UO_2 , PuO_2 (MOX) and in reactor transmutation matrices: $(Zr, An)O_2$

Single crystals as a simplified model of nuclear fuel or transmutation matrix

Simulation of radiation-induced damage

- Atomic collisions (MOSAIC platform IJCLab); electronic excitations (GANIL)
- Doping chemical contribution role played by soluble versus insoluble specie (fission products)





Kr (100 MeV)

Investigating the High Burnup Structure of spent nuclear fuels

- Microstructural phase transformation occurring at the rim of fuel pellets: grain subdivision (100 nm) and high porosity
- Related to the local enrichment in ²³⁹Pu (neutron capture cross section in the resonance region up to 1 eV)
- Atomic mechanisms not understood; possible parameters include low T, higher concentration of impurities, radiation damage (atomic and electronic)
- Parametric approach: burnup, T, chemistry of impurities, radiation defects

In situ channelling and TEM experiments coupled to implantation at 773 K – Role of insoluble versus soluble fission products

Swift ion irradiation coupled to channelling and TEM experiments – Role of electronic stopping



In situ channelling and TEM experiments coupled to implantation at 773 K – Role of insoluble versus soluble fission products

• Direct comparison between the fate of Xe and La (Z =54, insoluble in UO_2 ; Z = 57, fully soluble) - In situ TEM evolution (images recorded at 773 K)





Some dislocation

 Same evolution for both specie: sequential evolution from black dots to ^{lines} dislocation loops and lines







In situ channelling and TEM experiments coupled to implantation at 773 K – Role of insoluble versus soluble fission products

- Direct comparison between the fate of Xe and La (Z =54, insoluble in UO₂; Z = 57, fully soluble) In situ channelling evolution
- Defect model: RDA (obstruction) & BC (distortion)





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In situ channelling and TEM experiments coupled to implantation at 773 K – Role of insoluble versus soluble fission products

EXPERIMENTAL SIMULATION OF IRRADIATION INDUCED EFFECTS

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TEM



Images recorded in situ at 773 K at 5 dpa; mean bubble size is (2.0 \pm 0.5) nm

 Formation of Xe bubbles homogeneously distributed (no bubble or cavity for La)





Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

Low fluence range – Track formation (1 GeV Pb ions SME beam line)







zoom (×5)

10 nm

Hollowed tracks at surface

d ~ 4 nm

Filled tracks and dislocation loops along tracks

- Strong strain fields in the vicinity of tracks with presence of dislocation loops
- Evidence of 'hollowed' tracks in the crystal surface region (spatial extension ~ 100 nm)



Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

EXPERIMENTAL SIMULATION OF IRRADIATION INDUCED EFFECTS

Low fluence range – Track formation (1 GeV Pb ions)









80

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EXPERIMENTAL SIMULATION OF IRRADIATION INDUCED EFFECTS Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

Increasing the ion fluence range – Microstructural evolution – Nature of defect



$$\chi_D(z) = \chi_R(z) + (1 - \chi_R(z)) \frac{fn_D(z)}{n}$$

• Dechannelling parameter at depth z

$$\gamma(z) = \ln\left(\frac{1 - \chi_{V}(z)}{1 - \chi_{R}(z)}\right) = \ln\left(\frac{1 - \chi_{V}(z)}{1 - \chi_{D}(z)}\right) + \ln\left(1 - \frac{fn_{D}(z)}{n}\right) = \int_{0}^{z} \sigma_{D} n_{D}(z') dz'$$

• Present case: defects characterised by $f \neq 0$ but they are uniformly distributed in z (distribution is depth independent), $n_D(z) = n_D$

$$\gamma(z) = \gamma_{f=0}(z) + \ln\left(1 - \frac{fn_{D}}{n}\right)$$

• The energy dependence of the channelling parameter is given by the $\gamma_{f=0}$ (z) contribution, which is accessible to the experiment





EXPERIMENTAL SIMULATION OF IRRADIATION INDUCED EFFECTS Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

Increasing the ion fluence range – Microstructural evolution – Nature of defect



- Linear increase of γ with z: constant density of defects (in accordance with S_e)
 - At a (increa: increa: strain



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Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

Increasing the ion fluence range – Microstructural evolution – Nature of defects



- Direct impact model : $\gamma(\Phi) = \gamma^{S} [1 \exp(-\sigma\Phi)]$
- $ZrO_2 \sigma = 26 \text{ nm}^2$ (R = 2.9 nm); $UO_2 \sigma = 24 \text{ nm}^2$ (R = 2.8 nm)



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Swift ion irradiation coupled to channelling and TEM experiments 🖾 E&E Energie & Environ Investigating the role of electronic stopping





Swift ion irradiation coupled to channelling and TEM experiments 🖾 E&E Energy & Enviro Investigating the role of electronic stopping

- Increasing the ion fluence range Microstructural evolution Nature of defect
- Analysis of angular scans Monte Carlo simulation assuming the formation of domains (Λ_{\perp} , δ_{tilt}) over the entire thickness probed by RBS/C



Fluence (nm ⁻²)	Domain size (nm)		Mosaicity δ _{tilt} (deg.)	
	XRD	RBS-C	XRD	RBS- C
0.025	105	110	0.047	0.07
0.05	76	60	0.065	0.15
0.10	42	40	0.11	0.19
0.26	30	30	0.13	0.21





Investigating the High Burnup Structure of spent nuclear fuels

Irradiation experiments In situ channelling and TEM experiments coupled to implantation at 773 K – Role of insoluble versus soluble fission products

- First damage step is progressive: occurs for the same dpa for Xe and La and is due to atomic collisions (same evolution for both RDA and BC); it corresponds to the sequence formation of black dots defects, dislocation loops and lines
- Clear difference between soluble and insoluble specie: insoluble specie results in a higher fraction of RDA and BC associated to the formation of nanometre-sized Xe bubbles (difference in the saturation plateaus)
- Very important contribution at high fluence leading to polygonization of the structure induced by the presence of highly pressurised gas bubbles



Investigating the High Burnup Structure of spent nuclear fuels



Swift ion irradiation coupled to channelling and TEM experiments – Investigating the role of electronic stopping

- Similar behaviour for the two investigated fluorite-structured oxides Urania and Zirconia
- Track formation at low fluence: hillocks at the surface/hollowed tracks up to 100 nm
- Electronic stopping induced micrometre-size domains: in UO₂ (Λ_{\perp} , δ_{tilt}) = (30 nm; 0.15°); in ZrO₂ (Λ_{\perp} , δ_{tilt}) = (45 nm; 0.4°);
- Similar to the HBS in a genuine fuel but at higher electronic stopping : no chemical contribution required





Future experiments – Investigating the synergy between electronic and atomic contributions

Dual beam experiments performed at the JANNuS-Saclay facility

• UO₂ pellets bombarded simultaneously with low energy (atomic collisions) and medium energy (mostly electronic interactions) – TEM investigation





• Strong acceleration of formation and growth of dislocation loops while electronic energy deposition increases





Future experiments – Investigating the synergy between electronic and atomic contributions

Dual beam experiments performed at the JANNuS-Saclay facility

 UO₂ pellets bombarded simultaneously with low energy (atomic collisions) and medium energy (mostly electronic interactions) – Raman investigation



• Large decrease of the local disorder correlated with the increase in electronic energy deposition (decrease of uranium point defect concentration)





Experiments at GANIL, IJCLab, JANNuS-Saclay are possible thanks to the skills and dedication of technicians, engineers and physicists

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